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Determination of the resistivity anisotropy of $SrRuO_3$ by measuring the planar Hall effect

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We have measured the planar Hall effect in epitaxial thin films of the itinerant ferromagnet $SrRuO_3$ patterned with their current paths at different angles relative to the crystallographic axes. Based on the results, we have determined that $SrRuO_3$ exhibits small resistivity anisotropy in the entire temperature range of our measurements (between 2 to 300 K); namely, both above and below its Curie temperature (150 K). It means that in addition to anisotropy related to magnetism, the resistivity anisotropy of $SrRuO_3$ has an intrinsic, nonmagnetic source. We have found that the two sources of anisotropy have competing effects.

I. INTRODUCTION

The itinerant ferromagnet $SrRuO_3$ has attracted considerable experimental and theoretical effort for its intriguing properties; including, "bad metal" behavior[1, 2], deviation from normal metal optical conductivity [3] and negative deviation from Matthiessen's rule [4]. Consequently, there is growing interest in obtaining comprehensive characterization of its properties and in particular its transport behavior. Here we address a basic transport feature of $SrRuO_3$ as we use planar Hall effect measurements to determine quantitatively the existence of spontaneous resistivity anisotropy.

Being almost cubic, the few indications for spontaneous resistivity anisotropy in $SrRuO_3$ have been subtle and qualitative; for example, resistivities measured along [001] and $[1\bar{1}0]$ exhibit different critical behavior and they also seem to have slightly different values in the paramagnetic state [1]. These small differences imply that even if the anisotropy is real (and not due to spurious effects) it does not exceed few percents; hence, its quantitative determination is challenging.

In principle, obtaining quantitative characterization of spontaneous resistivity in a conductor can be achieved by direct measurements of the resistivity for different current directions. This method, however, is not very useful when the anisotropy is on the order of few percents, since it is affected by other sources (e.g., variations in geometrical factors and in the number and type of defects) whose contribution could be on the order of that of the intrinsic anisotropy. To overcome this difficulty, we deduce the intrinsic spontaneous resistivity anisotropy in $SrRuO_3$ by measuring the planar Hall effect (PHE) of this compound.

The PHE [5, 6, 7] is the appearance of transverse resistivity, ρ_{xy}, observed in conductors with resistivity anisotropy. In magnetic compounds it is usually related to the anisotropic magnetoresistance [7] which is the dependence of the longitudinal resistivity, ρ_{xx}, on the angle θ between the current and the internal magnetization. For many compounds it is found that:

$$\rho_{xx} = \rho_\perp + (\rho_\parallel - \rho_\perp)\cos^2\theta \text{ and}$$

$$\rho_{xy} = (\rho_\parallel - \rho_\perp)\cos\theta\sin\theta$$

where $\rho_\parallel$ and $\rho_\perp$ are the resistivities with the magnetization parallel and perpendicular to the current, respectively. However, simply measuring the transverse resistivity is also not sufficient since misalignment of contact leads would introduce a regular longitudinal contributions that is hard to distinguish from the transverse signal, since contrary to ordinary and extraordinary Hall effects, the planar Hall effect is symmetric under magnetization reversal, as is the longitudinal resistivity. Therefore, for reliable determination of the PHE one needs to demonstrate the expected dependence of the PHE on the angle between the current path and the principal axes of the resistivity tensor.

Despite being commonly associated with magnetism PHE is a phenomenon which arises whenever there is resistivity anisotropy and the current is not along one of the principal axes of the resistivity tensor; hence, it can be used to directly determine the intrinsic anisotropy of a conductor irrespective of the source of the anisotropy, including a non-magnetic source. However, if non-magnetic source of the anisotropy exists, one cannot rotate the direction of the principal axes of the resistivity tensor by changing the direction of an applied magnetic field. Therefor, we "rotate" the current path relative to the crystallographic axes by patterning current paths in different directions. Using this method, we have quantitatively determined the resistivity anisotropy of $SrRuO_3$ both above and below the Curie temperature and we have found that there are both magnetic and non-magnetic sources to the anisotropy with competing effects. The success of this method indicates that it could be a useful method for determining subtle anisotropy of other conductors, as well.

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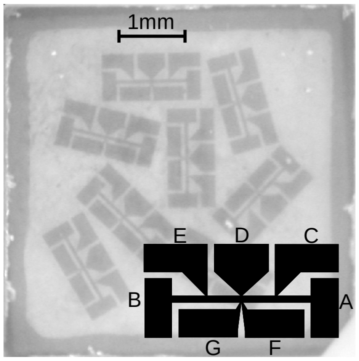

FIG. 1: Photo of the measured sample which consists of 8 patterns at different orientations. Inset: A scheme of an individual pattern.

II. MEASUREMENTS AND DISCUSSION

Our samples are epitaxial films of $SrRuO_3$ grown on slightly miscut (2°) $SrTiO_3$. The films are orthorhombic ($a = 5.53$ Å, $b = 5.57$ Å, $c = 7.85$ Å) [8] and their Curie temperature is ~ 150 K. The films grow with the in-plane c axis perpendicular to the miscut, and a and b axes at 45 degrees relative to the film plane. The films exhibit uniaxial magnetocrystalline anisotropy with the easy axis close to the b axis [8]. These are twin-free films whose high quality has been previously manifested, including in exhibiting low-temperature magnetoresisitance quantum oscillations [9].

The data presented here are from a 27 nm thick film with resisitivity ratio of ~ 12 on which there are 8 identical patterns, each along a different crystallographic direction in the (110) plane. The angles of the patterns relative to the $[1\bar{1}0]$ axis (in the film plane) are: -45 ,0, 15, 30, 45, 60, 75 and 90 degrees. Each pattern allows longitudinal and transverse resistivity measurements (see Figure 1).

The resistance measured between the pads marked F and D, R_{FD}, has several contributions: a) longitudinal resistance due to longitudinal shift between the two leads b) ordinary Hall effect [OHE] and extraordinary Hall effect [EHE] [11] due to magnetic field and magnetization, and c) PHE. According to the pattern design, the longitudinal resistance should be half the resistance between F and G, R_{FG}; therefore, it can be subtracted. The OHE and EHE are antisymmetric signals; hence, they are determined by interchanging current and voltage leads [12]. Figure 2a. shows R_{FD} as a function of temperature for all the patterns. The measurements are at zero applied field after field cooling to avoid contribution of magnetic domain walls to resisitivity [13]. The antisymmetric contribution to R_{FD} (obtained by current and voltage interchange) for all the patterns is shown in Figure 2b. Since the applied field is zero, the obtained signal is the EHE. We see that this contribution is almost identical for all patterns (and consistent with previous reports [14]) indicating that, as expected, only the perpendicular component of the magnetization, which is identical for all patterns, is relevant. In Figure 2c we show the PHE for all the patterns after subtracting the antisymmetric part and the expected contribution due to longitudinal resistance.

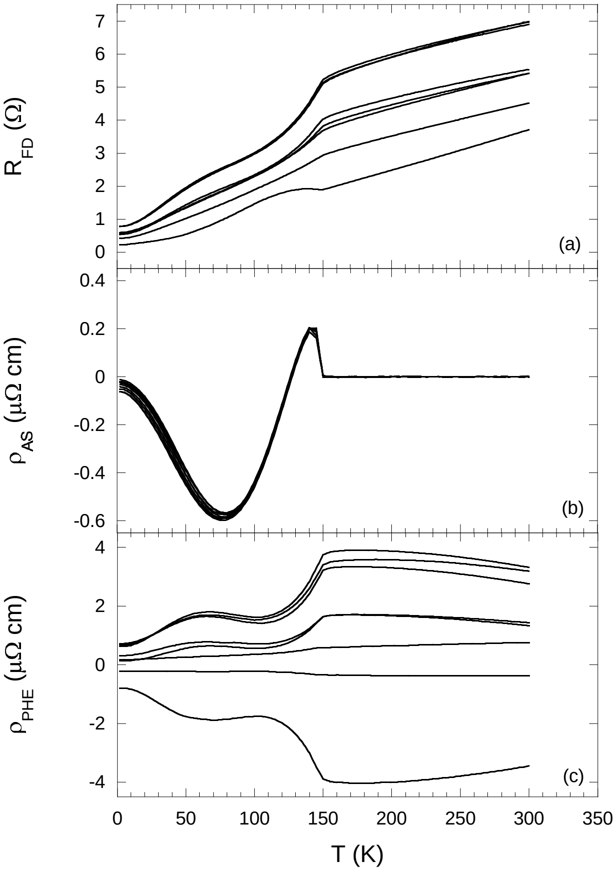

FIG. 2: a) R_{FD} as a function of temperature for the 8 patterns. In decreasing order of R_{FD} value at 300 K the curves correspond to patterns at angles of : 45, 30, 15, 0, 75 90 and -45 degrees b) The antisymmetric contribution to R_{FD}. c) PHE contribution to R_{FD}. In decreasing order of their value at 300 K the curves correspond to patterns at angles of : 45, 60, 30, 15, 75, 0, 90 and -45 degrees.

We note that the PHE curves exhibit similar qualitative angular dependence with the largest PHE obtained for $\theta = \pm 45^\circ$ and the smallest for $\theta = 0^\circ, 90^\circ$. This indicates that the resistivities in the 0° and 90° directions, ρ_0 and ρ_{90}, are the principal axes of resistivity and we expect that at each temperature the PHE for current in the θ direction will obey $\rho_{xy} = (\rho_0 - \rho_{90}) \sin\theta \cos\theta$. It also means that between any two PHE curves obtained for patterns at angles θ_1 and θ_2 there will be temperature-independent proportionality given by $\cos\theta_1 \sin\theta_1 / \cos\theta_2 \sin\theta_2$.

As noted above, the longitudinal resistance contribution to R_{FD} should be $a \times R_{FG}$ with $a = 0.5$. However, minute lithography variations may slightly change this factor. If the correct longitudinal contribution is precisely determined for all angles, we expect that all the PHE curves will be proportional to each other. There-

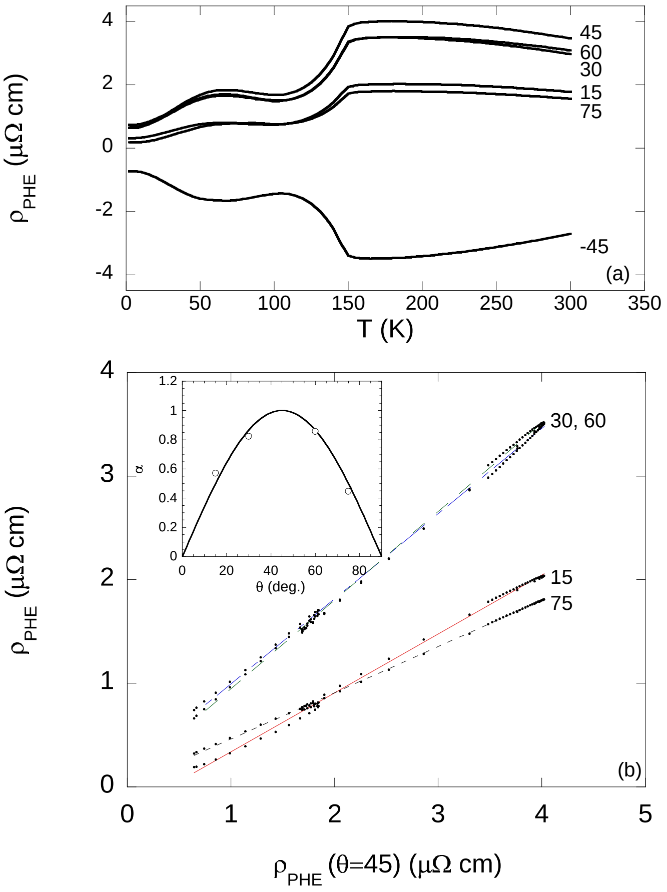

FIG. 3: a) Refined PHE (see text) vs temperature. The number near the curve indicates the pattern orientation. b) The PHE in patterns oriented at various angels vs the PHE in the pattern oriented at 45 degrees. The lines are linear fits. Inset: The slope of the linear fits , α, as a function of θ. The line is the expected sinθcosθ dependence.

fore, we use MATLAB for refining ”a” within few percents in order to obtain the simultaneously best proportionality between the data sets of PHE obtained for the different angles. The process does not impose the magnitude of the proportionality factor. Figure 3a. shows the PHE for all the angles after the refinement. To show the proportionality we present in Figure 3b the PHE at various angles as a function of the PHE obtained for $\theta = 45^\circ$. The inset of Figure 3b shows the proportionality factor as a function of the pattern angle where the solid line is sinθcosθ (with no adjustable parameters). This remarkable consistency obtained between all PHE curves strongly supports the reliability of the obtained PHE curve.

Figure 4 presents the resistivity anisotropy as obtained from the PHE. The results show that in the entire temperature range of our measurements (2 to 300 K) ρ_0 (along [110]) is larger than ρ_{90} (along [001]). As a consistency check we show that if we allow for small adjustments of few percents, we can correlate the PHE with the difference between ρ_{xx} measured at different angles. The agreement is very satisfactory in view of the effect of other sources on the variations between different patterns, such as different defect concentration. It should be noted that only the fact that we have determined the anisotropy by PHE measurements allowed us to make the small adjustments in the longitudinal resistivities.

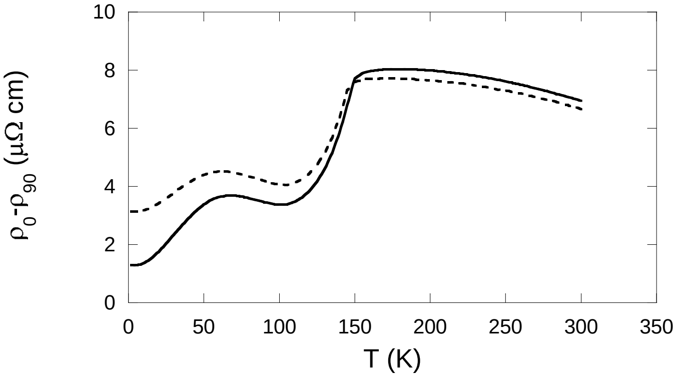

FIG. 4: The anisotropy $\rho_0 - \rho_{90}$ as determined by PHE measurements (continues) and from subtraction of longitudinal resistivities (dashed).

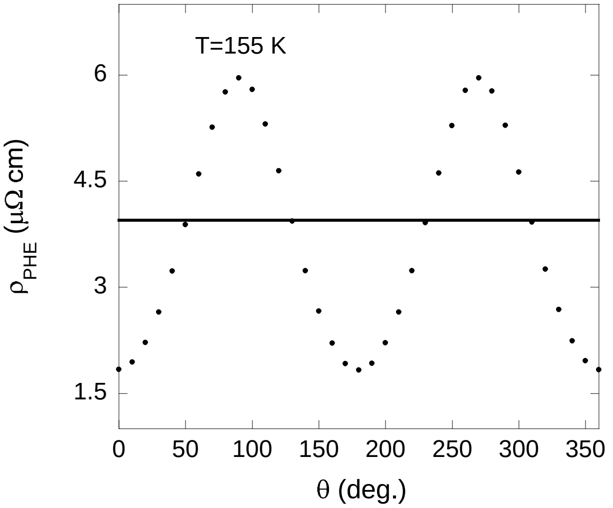

FIG. 5: The PHE for the pattern oriented at 45 degrees at 155 K as a function of θ, the angle between an in-plane 8 T field and [1$\bar{1}$0]. The dashed line is the zero field value of the PHE.

An interesting and somewhat surprising observation is that the anisotropy persists in the paramagnetic state. Despite the lack of long range order in the paramagnetic state one cannot exclude a priori magnetic origin for the paramagnetic anisotropy in view of the observed anisotropic paramagnetic susceptibility [10]. To address possible magnetic origin we examine the dependence of the anisotropy on magnetization in the paramagnetic state.

Figure 5 shows the change in PHE (namely the anisotropy) when a field of 8 T is rotated in the film plane above the Curie temperature at 155 K. The PHE

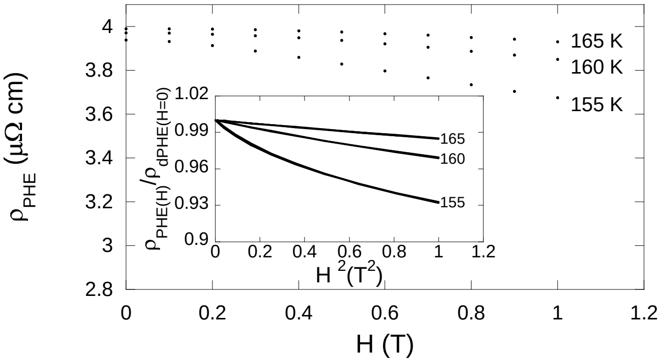

FIG. 6: a) The PHE for the 45 degrees oriented pattern vs H at 155, 160 and 165 K. Inset: PHE normalized by its zero-field value as a function of H^2 for all the patterns.

of the pattern oriented at 45 degrees varies considerably with the rotation of the field. However, the sign of the anisotropy remains unchanged despite the fact that the magnetization completes a full rotation. This clearly indicates that in addition to magnetism there is also non-magnetic source of the resistivity anisotropy.

Figure 6 shows the effect of applying a magnetic field in the paramagnetic state along the b axis which is the easy axis of magnetization. We see that the PHE decreases as the induced magnetization increases. The inset shows the relative change in the PHE for all patterns as a function of H^2. We note that all patterns show the same field dependence, as expected from the fact that all PHE values are related by temperature-independent and field-independent constants. At higher temperatures we see also that the magnetically-related anisotropy is proportional to H^2; namely, to M^2. The fact that the induced magnetization decreases the PHE indicates that the magnetic and non-magnetic sources of anisotropy have opposite effects. In view of this observation, the sharp decrease in the zero-field PHE when temperature decreases below T_c is understood as a result of the onset of spontaneous magnetization.

In the paramagnetic state we see a gradual decrease of the PHE with increasing temperature. The anisotropy is probably related to the deviation from cubic structure. Studies have shown that $SrRuO_3$ films grown on $SrTiO_3$ undergo two structural phase transitions orthorhohmbic to tetragonal at $\sim 350°$ C and tetragonal to cubic at $\sim 600°$ C [15]. Therefore, 600° C is the upper limit for the observed anisotropy.

III. CONCLUSIONS

By measuring the planar Hall effect on patterns with current paths oriented in different crystallographic directions we were able to determine both magnetic and non-magnetic sources of anisotropy present in epitaxial films of $SrRuO_3$. We find the the in-plane principal axes are $[1\bar{1}0]$ and [001]. That non-magnetic anisotropy makes the resistivity along $[1\bar{1}0]$ larger while spontaneous magnetization (along [010]) decreases this anisotropy.

Acknowledgments

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